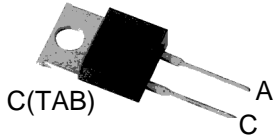


STPR805DB thru STPR820DB

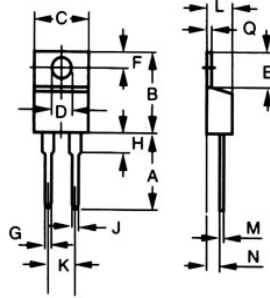
Ultra Fast Recovery Diodes



A=Anode, C=Cathode, TAB=Cathode

	V _{RRM} V	V _{RMS} V	V _{DC} V
STPR805DB	50	35	50
STPR810DB	100	70	100
STPR815DB	150	105	150
STPR820DB	200	140	200

Dimensions TO-220AC



Dim.	Inches		Millimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.580	12.70	14.73
B	0.560	0.650	14.23	16.51
C	0.380	0.420	9.66	10.66
D	0.139	0.161	3.54	4.08
E	2.300	0.420	5.85	6.85
F	0.100	0.135	2.54	3.42
G	0.045	0.070	1.15	1.77
H	-	0.250	-	6.35
J	0.025	0.035	0.64	0.89
K	0.190	0.210	4.83	5.33
L	0.140	0.190	3.56	4.82
M	0.015	0.022	0.38	0.56
N	0.080	0.115	2.04	2.49
Q	0.025	0.055	0.64	1.39

Symbol	Characteristics	Maximum Ratings	Unit
I _{AV}	Maximum Average Forward Rectified Current @T _c =125°C	8.0	A
I _{FSM}	Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)	100	A
V _F	Maximum Forward Voltage I _F =8A @T _J =25°C @T _J =150°C	1.3 0.8	V
I _R	Maximum DC Reverse Current At Peak Reverse Voltage @T _J =25°C @T _J =100°C	10 500	uA
C _J	Typical Junction Capacitance (Note 1)	45	pF
T _{RR}	Maximum Reverse Recovery Time (Note 2)	25	ns
R _{θJC}	Typical Thermal Resistance (Note 3)	3.0	°C/W
T _J , T _{STG}	Operating And Storage Temperature Range	-55 to +150	°C

NOTES: 1. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.

2. Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A.

3. Thermal Resistance Junction To Case.

FEATURES

- * Glass passivated chip
- * Superfast switching time for high efficiency
- * Low forward voltage drop and high current capability
- * Low reverse leakage current
- * High surge capacity

MECHANICAL DATA

- * Case: TO-220AC molded plastic
- * Polarity: As marked on the body
- * Weight: 0.08 ounces, 2.24 grams
- * Mounting position: Any



STPR805DB thru STPR820DB

Ultra Fast Recovery Diodes

